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☐ 1. Document ID: US 5814533 A

L13: Entry 1 of 2 File: EPAB Sep 29, 1998

DOCUMENT-IDENTIFIER: US 5814533 A
TITLE: Semiconductor light emitting element and manufacturing method therefor

Abstract (1):
CHG DATE=19990617 STATUS=N>A manufacturing method of semiconductor light emitting element including the steps of: (a) laminating a gallium nitride compound semiconductor layer for forming a luminous part on a substrate including at least an n-type layer and a p-type layer, by organic metal compound vapor phase growth method, (b) forming the gallium nitride compound semiconductor layer in a nitrogen gas atmosphere after laminating, and lowering the ambient temperature to the temperature for growing a GaAs compound in vapor phase and annealing the p-type layer of the gallium nitride compound semiconductor, (c) forming a film of at least one type selected from the group consisting of GaAs, GaP, InAs, InP, all doped with Mg, and part of these group III elements replaces by Al. on the surface of the gallium nitride compound semiconductor layer, as a protective layer in the nitrogen atmosphere, and (d) annealing the p-type layer of gallium nitride compound semiconductor layer simultaneously with forming the protective film, and lowering to room temperature after annealing, and removing the protective film by etching.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Desc | Image

☐ 2. Document ID: EP 678945 A1

L13: Entry 2 of 2 File: EPAB Oct 25, 1995

DOCUMENT-IDENTIFIER: EP 678945 A1
TITLE: Gallium nitride group compound semiconductor laser diode.

Abstract (1):
CHG DATE=19990617 STATUS=O> A gallium nitride group compound semiconductor laser diode (10) satisfying the formula (AlxGa1-x)yIn1-yN, inclusive of 0 magnesium (Mg) doped p-type conductive gallium nitride group compound semiconductor satisfying the formula (AlxGa1-x)yIn1-yN, inclusive of 0 doped with silicon (Si). As a result, luminous efficiency is improved and threshold current for oscillation is lowered.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Desc | Image

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